



DNLS350

LOW VCE(SAT) NPN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 60V
- I_C = 3.0A High Continuous Current
- Extremely Low Equivalent On-Resistance; $R_{CE(SAT)}$ 62m Ω at 2A
- Complementary PNP Type: DPLS350E
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

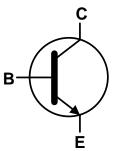
Applications

Ideal for Medium Power Switching or Amplification Applications

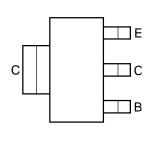




Top View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

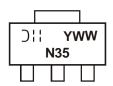
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DNLS350E-13	AEC-Q101	N35	13	12	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



N35 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 15 = 2015) WW = Week Code (01 - 52)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	3	Α
Peak Pulse Collector Current	Ісм	5	Α
Peak Pulse Base Current	I _{BM}	1	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)	3			
Power Dissipation	(Note 6)	P_{D}	2	W	
	(Note 7)		1		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	62.5	°C/W	
	(Note 7)		125		
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	15	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

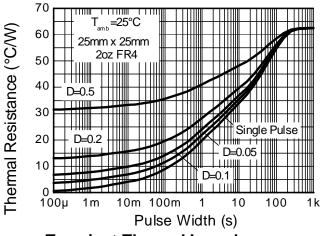
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

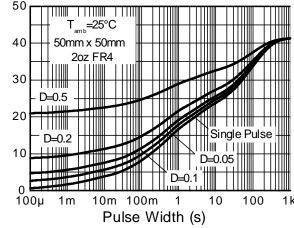
Notes:

- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 Same as Note (5), except mounted on 25mm x 25mm 2oz copper.
 Same as Note (5), except mounted on minimum recommended pad (MRP) layout.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



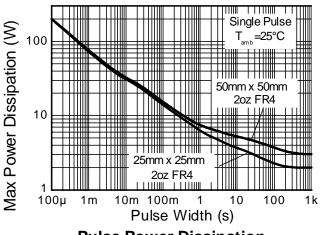
Thermal Characteristics and Derating Information

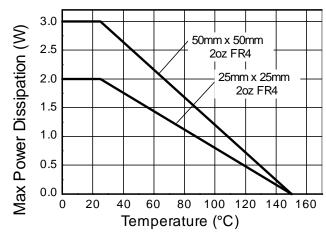




Transient Thermal Impedance







Pulse Power Dissipation

Derating Curve

Thermal Resistance (°C/W)



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	50	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	I _E = 100μA
Collector-Base Cutoff Current		_	_	100	nA	$V_{CB} = 50V, I_{E} = 0$
Collector-Base Cutoff Current	I _{CBO}	_	_	50	μΑ	$V_{CB} = 50V, I_{E} = 0, T_{A} = +150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)						
		200	_	_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h _{FE}	200	_	_		V _{CE} = 2V, I _C = 1A
		100	_	_		$V_{CE} = 2V$, $I_C = 2A$
		_	_	90	mV	$I_C = 0.5A$, $I_B = 50mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	170		$I_C = 1A, I_B = 50mA$
		_	_	290		I _C = 2A, I _B = 200mA
Equivalent On-Resistance	R _{CE(SAT)}	_	62	145	mΩ	I _C = 2A, I _B = 200mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	1.2	V	I _C = 2A, I _B = 200mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	1.1	V	V _{CE} = 2V, I _C = 1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	C _{obo}	_	_	30	pF	V _{CB} = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

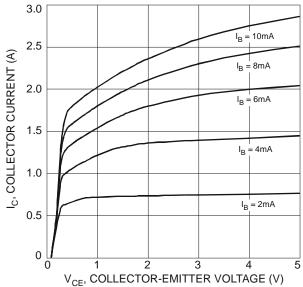
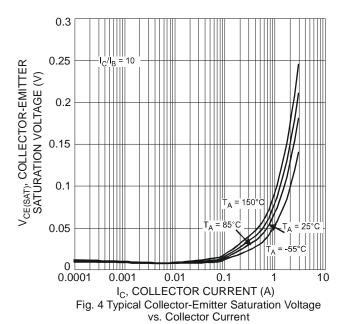


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



700 600 = 150°C h_{FE}, DC CURRENT GAIN 500 = 85°C 400 T_Δ = 25°C 300 200 T_A = -55°C 100 0.001 0.01 0.1 10 I_C, COLLECTOR CURRENT (A)

Fig. 3 Typical DC Current Gain vs. Collector Current

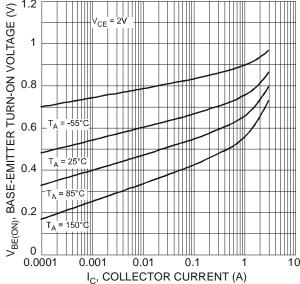


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



Typical Electrical Characteristics (Continued) (@T_A = +25°C, unless otherwise specified.)

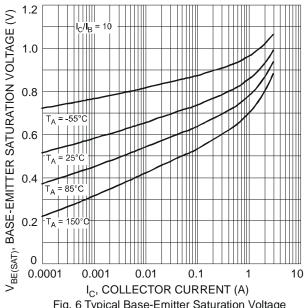


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

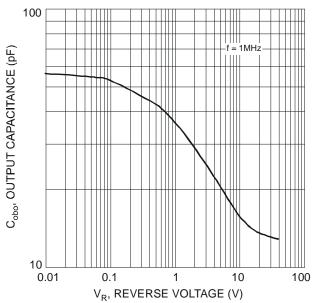
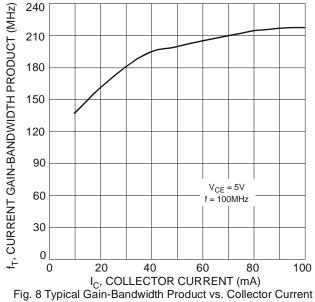


Fig. 7 Typical Output Capacitance Characteristics

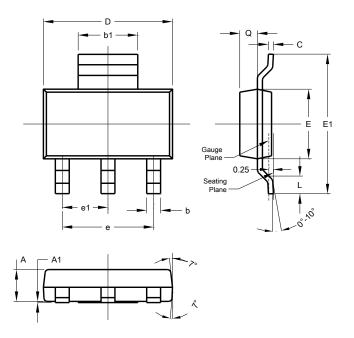




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT223

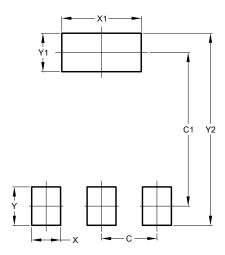


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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